

**SMC Schottky Barrier Rectifier Diode 肖特基势垒整流二极管**

**■ Features 特点**

Low forward voltage drop 低正向压降  
High current capability 高电流能力  
Surface mount device 表面贴装器件  
Case 封装:SMC(DO-214AB)



**■ Maximum Rating 最大额定值**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	SS 82C	SS 83C	SS 84C	SS 85C	SS 86C	SS 88C	SS 89C	SS 810C	Unit 单位
Marking 印字		SS82	SS83	SS84	SS85	SS86	SS88	SS89	SS810	
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	$V_R$	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	$I_F$	8								A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	175								A
Thermal Resistance J-L 结到管脚热阻	$R_{\theta JL}$	10								$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	$T_J$	150								$^{\circ}\text{C}$
Storage Temperature 储藏温度	$T_{stg}$	-65to+150 $^{\circ}\text{C}$								$^{\circ}\text{C}$

**■ Electrical Characteristics 电特性**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	SS82C-SS84C	SS85C-SS86C	SS88C-SS810C	Unit 单位	Condition 条件
Forward Voltage 正向电压	$V_F$	0.55	0.70	0.85	V	$I_F=8\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$ $(100^{\circ}\text{C})$	0.1 5		0.02 2	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$	380			pF	$V_R=4\text{V}$ , $f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

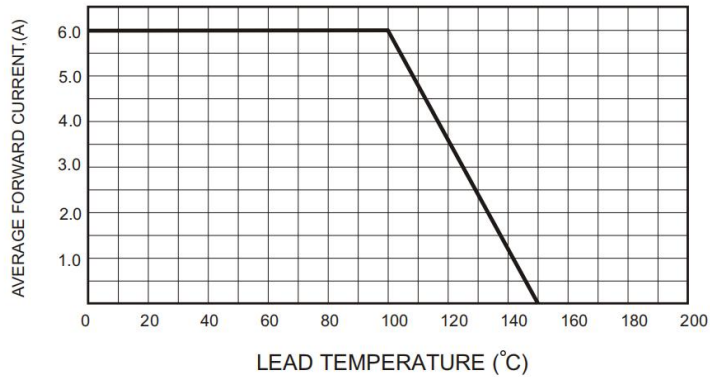


Fig.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

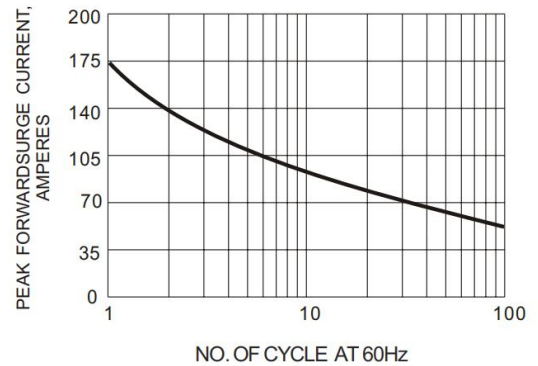


FIG.3-TYPICAL FORWARD CHARACTERISTICS

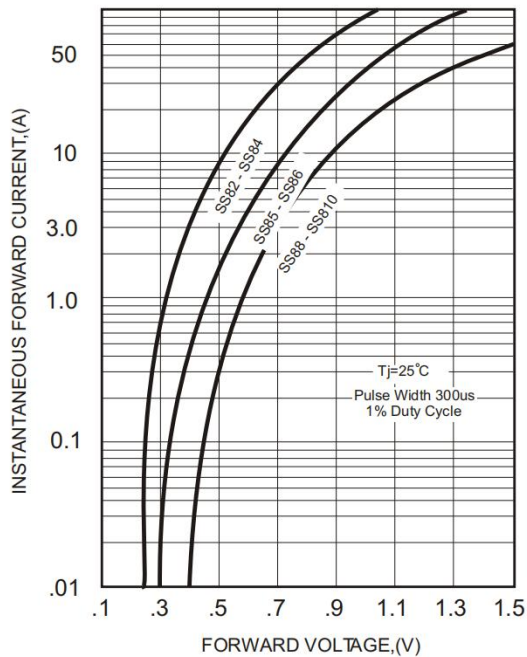
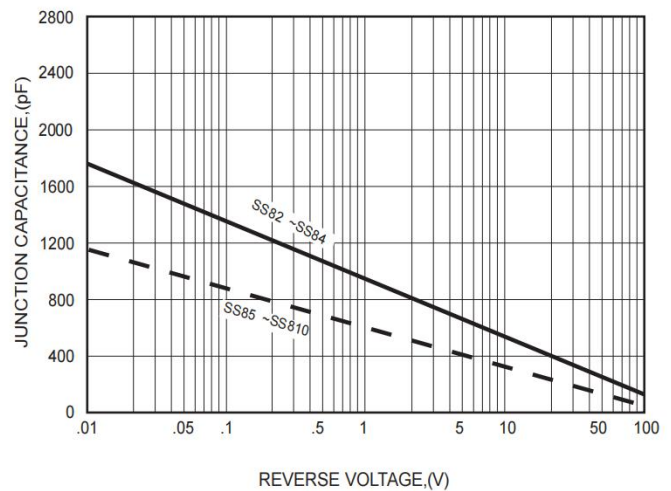
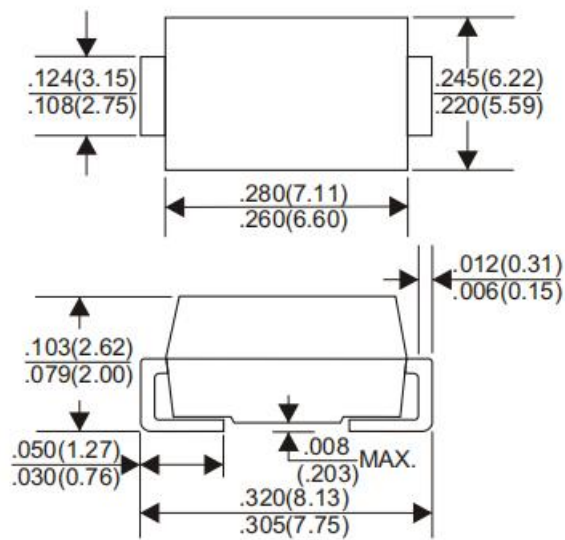


FIG.4-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AB(SMC)



Dimensions in inches and (millimeters)